1. Record Nr. UNISA996466080003316

Autore	Mira J (Jose)
Titolo	Tasks and methods in applied artificial intelligence / / Angel Pasqual del Pobil, Jose Mira, Moonis Ali, eds
Pubbl/distr/stampa	Springer Berlin / Heidelberg
ISBN	978-3-540-69350-5 3-540-64574-8
Altri autori (Persone)	PobilAngel Pasqual del xiraJ (Jose) AliMoonis
Soggetti	Artificial intelligence - Congresses Artificial intelligence - Industrial applications - Congresses Expert systems (Computer science) - Congresses
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia

2. Record Nr. UNISA996336747803316

Titolo	Enseñanza de las ciencias sociales
Pubbl/distr/stampa	Barcelona : , : Institut de Ciències de l'Educació, , 2002-
ISSN	2014-7694
Descrizione fisica	1 online resource
Soggetti	Social sciences - Study and teaching History - Study and teaching Geography - Study and teaching Periodicals.
Lingua di pubblicazione	Spagnolo
Formato	Materiale a stampa
Livello bibliografico	Periodico
Note generali	Refereed/Peer-reviewed "Revista de investigación."

3. Record Nr. UNINA9910490029703321

Titolo	Community Empowerment through Research, Innovation and Open Access : Proceedings of the 3rd International Conference on Humanities and Social Sciences (ICHSS 2020), Malang, Indonesia, 28 October 2020 / / edited by Joko Sayono [and six others]
Pubbl/distr/stampa	London : , : Routledge, , 2021
ISBN	1-00-318920-2 1-000-41578-3 1-003-18920-2
Descrizione fisica	1 online resource (180 pages) : illustrations (black and white)
Disciplina	307.14
Soggetti	Community development Political participation
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references.
Sommario/riassunto	ICHSS is an international seminar that is held every two years organized by the Research and Community Service Institute of the State University of Malang. The meeting aims to discuss the theoretical and practical developments of Social Sciences and Humanities in Indonesia and other countries with a view to build academic networks by gathering academics from various research institutes and universities.Community empowerment serves as a trigger to increase community independence and to cope with the challenges resulting from the rapid development of technology. An important aspect of the community empowerment effort is to link the results of innovation research for the benefit of community. The results of research should not only be limited to publications in the academic environment. Open Access to various forms of the existing literature is one of the requirements for innovative research to develop optimally. Therefore, this seminar has also served as a place for field researchers from various geographical areas to socialize, to discuss and to find solutions to current issues in the field of social sciences and humanities, as well as to build

		cooperation and synergy in creating ideas for mutual collaboration and to create joint research.

4.	Record Nr.	UNINA9910829904303321
	Titolo	Power electronics semiconductor devices [[electronic resource] /] / edited by Robert Perret
	Pubbl/distr/stampa	London, : ISTE Hoboken, NJ, : Wiley, 2009
	ISBN	1-282-25383-2 9786613814487 0-470-61149-9 0-470-39414-5
	Descrizione fisica	1 online resource (569 p.)
	Collana	ISTE ; ; v.66
	Altri autori (Persone)	PerretRobert
	Disciplina	621.381/044 621.38152
	Soggetti	Power electronics Power semiconductors Solid state electronics
	Lingua di pubblicazione	Inglese
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
	Note generali	Description based upon print version of record.
	Nota di bibliografia	Includes bibliographical references and index.
	Nota di contenuto	Power Electronics Semiconductor Devices; Table of Contents; Preface; Chapter 1. Power MOSFET Transistors; 1.1. Introduction; 1.2. Power MOSFET technologies; 1.2.1. Diffusion process; 1.2.2. Physical and structural MOS parameters; 1.2.3. Permanent sustaining current; 1.3. Mechanism of power MOSFET operation; 1.3.1. Basic principle; 1.3.2. Electron injection; 1.3.3. Static operation; 1.3.4. Dynamic operation; 1.4. Power MOSFET main characteristics; 1.5. Switching cycle with an inductive load; 1.5.1. Switch-on study; 1.5.2. Switch-off study 1.6. Characteristic variations due to MOSFET temperature changes1.7. Over-constrained operations; 1.7.1. Overvoltage on the gate; 1.7.2. Over-current; 1.7.3. Avalanche sustaining; 1.7.4. Use of the body diode; 1.7.5. Safe operating areas; 1.8. Future developments of the

power MOSFET; 1.9. References; Chapter 2. Insulated Gate Bipolar Transistors; 2.1. Introduction; 2.2. IGBT technology; 2.2.1. IGBT structure; 2.2.2. Voltage and current characteristics; 2.3. Operation technique; 2.3.1. Basic principle; 2.3.2. Continuous operation; 2.3.3. Dynamic operation; 2.4. Main IGBT characteristics
2.5 One cycle of hard switching on the inductive load2.5.1. Switch-on study; 2.5.2. Switch-off study; 2.6 Soft switching study; 2.6.1. Soft switching switch-on: ZVS (Zero Voltage Switching); 2.6.2. Soft switching switch-off: ZCS (Zero Current Switching); 2.7. Temperature operation; 2.8. Over-constraint operations; 2.8.1. Overvoltage; 2.8.2. Over-current; 2.8.3. Manufacturer's specified safe operating areas; 2.9. Future of IGBT; 2.9.1. Silicon evolution; 2.9.2. Saturation voltage improvements; 2.10. IGBT and MOSFET drives and protections; 2.10.1. Gate drive design; 2.10.2. Gate drive circuits
2.10.3. MOSFET and IGBT protections2.11. References; Chapter 3. Series and Parallel Connections of MOS and IGBT; 3.1. Introduction; 3.2. Kinds of associations; 3.2.1. Increase of power; 3.2.2. Increasing performance; 3.3. The study of associations: operation and parameter influence on imbalances in series and parallel; 3.3.1. Analysis and characteristics for the study of associations; 3.3.2. Static operation; 3.3.3. Dynamic operation: commutation; 3.3.4. Transient operation; 3.3.5. Technological parameters that influence imbalances; 3.4. Solutions for design; 3.4.1. Parallel association
3.4.2. Series associations3.4.3. Matrix connection of components; 3.5. References; Chapter 4. Silicon Carbide Applications in Power Electronics; 4.1. Introduction; 4.2. Physical properties of silicon carbide; 4.2.1. Structural features; 4.2.2. Chemical, mechanical and thermal features; 4.2.3. Electronic and thermal features; 4.2.4. Other "candidates" as semiconductors of power; 4.3. State of the art technology for silicon carbide power components; 4.3.1. Substrates and thin layers of SiC; 4.3.2. Technological steps for achieving power components
4.4. Applications of silicon carbide in power electronics

Sommario/riassunto

This book relates the recent developments in several key electrical engineering R&D labs, concentrating on power electronics switches and their use. The first sections deal with key power electronics technologies, MOSFETs and IGBTs, including series and parallel associations. The next section examines silicon carbide and its potentiality for power electronics applications and its present limitations. Then, a dedicated section presents the capacitors, key passive components in power electronics, followed by a modeling method allowing the stray inductances computation, necessary for the precise